

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-42. (Canceled)

43. (New) A method for manufacturing a wiring substrate, comprising:

 a first step of ejecting a plurality of first droplets containing a functional material from a nozzle of a first head, and disposing the first droplets on a fixing surface of the substrate at intervals at which the first droplets do not come into contact with each other;

 a second step of, after the first step, irradiating each of the first droplets disposed on the fixing surface with a first laser beam;

 a third step of, after the second step, disposing a second droplet containing the functional material between the first droplets; and

 a fourth step of, after the third step, irradiating the first droplets and the second droplet with a second laser beam having an intensity greater than that of the first laser beam to fire the first droplets and the second droplet, forming a conductive film containing the functional material,

 wherein a part of each first droplet is gasified by irradiating each first droplet with the first laser beam at the second step, and the viscosity of each first droplet increases by gasifying the part of the first droplets.

44. (New) The method for manufacturing a wiring substrate according to claim 43, wherein the third step is performed using a second head.

45. (New) A method for manufacturing a wiring substrate, comprising:

 a first step of ejecting a first droplet containing a functional material from a nozzle of a first head to dispose the first droplet on a fixing surface of the substrate;

a second step of, after the first step, irradiating the first droplet disposed on the fixing surface with a first laser beam; and

a third step of, after the second step, irradiating the first droplet with a second laser beam having an intensity greater than that of the first laser beam to fire the first droplet, forming a conductive film containing the functional material,

wherein a part of the first droplet is gasified by irradiating the first droplet with the first laser beam at the second step, and the viscosity of the first droplet increases by gasifying the part of the first droplet.

46. (New) The method for manufacturing a wiring substrate according to claim 45, further comprising:

a disposing step of, after the second step, ejecting a second droplet containing the functional material from the nozzle of the first head to overlap with a part of the first droplet; and

an irradiating step of irradiating the second droplet disposed on the fixing surface with the first laser beam,

wherein a part of the second droplet is gasified by irradiating the second droplet with the first laser beam at the irradiating step, the viscosity of the second droplet increases by gasifying the part of the second droplet, and the third step includes firing the second droplet with the increased viscosity.

47. (New) The method for manufacturing a wiring substrate according to claim 45, wherein the first droplet contains a photothermal conversion material, and the first laser beam has a wavelength in the absorption band for the photothermal conversion material.

48. (New) The method for manufacturing a wiring substrate according to claim 45, wherein the first laser beam is applied to the substrate from a surface of the substrate on a side facing the first head.

49. (New) The method for manufacturing a wiring substrate according to claim 45, wherein:

the substrate is a transparent substrate; and
the first laser beam is applied to the substrate from a surface of the substrate on a side opposite the side facing the first head.

50. (New) The method for manufacturing a wiring substrate according to claim 45, wherein:

the first head has a plurality of the nozzles, the plurality of the nozzles ejecting a plurality of the first droplets; and
a plurality of the first laser beams is formed using a semiconductor laser array formed by a plurality of semiconductor lasers arranged in an array, and the plurality of the first droplets is irradiated with the plurality of the first laser beams.

51. (New) The method for manufacturing a wiring substrate according to claim 45, wherein:

the first head has a plurality of the nozzles, the plurality of the nozzles ejecting a plurality of the first droplets;

a plurality of the first laser beams is formed using a semiconductor laser array formed by a plurality of semiconductor lasers arranged in an array;

the method includes an adjusting step of rotating the semiconductor laser array around the normal of the fixing surface before the first step to adjust the intervals of the plurality of the first laser beams so as to match the arrangement pitch of the plurality of the first droplets; and

the plurality of the first droplets is irradiated with the plurality of the first laser beams.

52. (New) The method for manufacturing a wiring substrate according to claim 45, wherein:

the first laser beam and the second laser beam are the same type of laser beam; and

the second step and the third step are performed consecutively.

53. (New) A method for manufacturing an electro-optic apparatus, comprising using a method for manufacturing a wiring substrate according to claim 43.

54. (New) A method of manufacturing an electronic device, comprising using a method for manufacturing a wiring substrate according to claim 43.

55. (New) A droplet ejecting apparatus, comprising:

a head including:

a piezoelectric element;

a pressure chamber having the piezoelectric element attached thereto, that holds a liquid; and

a nozzle, provided in the pressure chamber, that separates a part of the liquid to eject it as a droplet;

a laser beam source; and

a reflector that applies a laser beam emitted from the laser beam source to a location of impact of the droplet ejected from the nozzle.

56. (New) The droplet ejecting apparatus according to claim 55, wherein the laser beam has a wavelength in the infrared region.

57. (New) The droplet ejecting apparatus according to claim 55, wherein the intensity distribution of the laser beam has a ring-like, elliptic, or rod-like shape.

58. (New) The droplet ejecting apparatus according to claim 55, wherein the laser beam has a beam profile in which the intensity on the outer edge of the irradiated region is higher than that on the inside.

59. (New) An apparatus for manufacturing a wiring substrate, comprising a droplet ejecting apparatus according to claim 55.